

InAsSbP Photodiodes for 2.6–2.8- μm Wavelengths

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Abstract—Research data for photovoltaic, I – V , and C – V characteristics of InAsSbP/InAs heterostructure photodiodes that operate at room temperature in the wavelength range 2.6–2.8 μm have been reported. Based on these data and available publications, conclusions have been drawn about the prospects for using these photodiodes in a number of applications.

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